



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	20mΩ @ V _{GS} = 10V	7.7A
30V	$32m\Omega$ @ $V_{GS} = 4.5V$	6.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

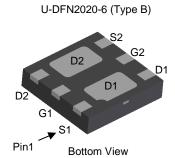
- General Purpose Interfacing Switch
- Power Management Functions

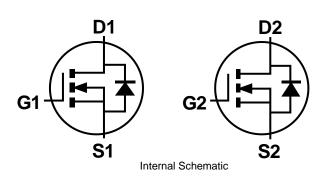
Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (4)
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)





Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3020LFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMT3020LFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Y2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	201	5	2016		2017	20	18	2019		2020		2021
Code	С		D		Е		F	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	1	5	6	7	8	9	0	N	D



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	7.7 6.2	А	
Maximum Continuous Body Diode Forward Curren	t (Note 6)	Is	2	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1	l%)	I _{DM}	50	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	170	°C/W
Total Power Dissipation (Note 6)		P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	70	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

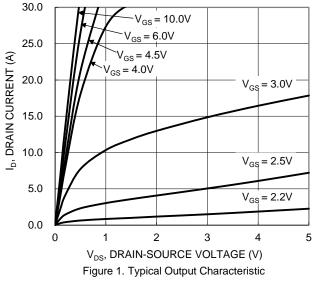
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

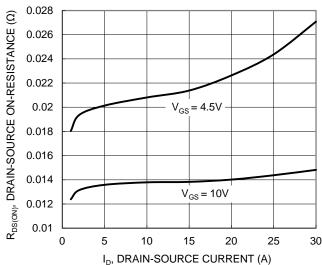
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)						•	
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V$, $I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance				20	mΩ	$V_{GS} = 10V, I_D = 9.0A$	
Static Dialit-Source Off-Resistance	R _{DS} (ON)	_		32	11122	$V_{GS} = 4.5V, I_D = 7.0A$	
Diode Forward Voltage	V_{SD}	_	_	1.0	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C_{ISS}	_	393	_	pF	15)()(
Output Capacitance	Coss	_	173	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C_{RSS}	_	27	_	pF	1 = 1.000112	
Gate Resistance	R_{G}	_	1.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_G	_	7.0	_	nC		
Total Gate Charge (V _{GS} = 4.5V)	Q_G	_	3.6	_	nC	7, 45,4 04	
Gate-Source Charge	Q_GS	_	0.9	_	nC	$V_{DD} = 15V, I_{D} = 9A$	
Gate-Drain Charge	Q_GD	_	1.5	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	1.8	_	ns		
Turn-On Rise Time	t _R	_	1.9	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	7.5	_	ns	$R_G = 6\Omega$, $I_D = 9A$	
Turn-Off Fall Time	t _F	_	2.4	_	ns	7	
Reverse Recovery Time	t _{RR}	_	10	_	ns		
Reverse Recovery Charge	Q _{RR}	_	2.6	<u> </u>	nC	$I_F = 9A$, di/dt = 100A/ μ s	

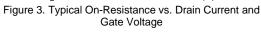
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25$ °C.
- 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.









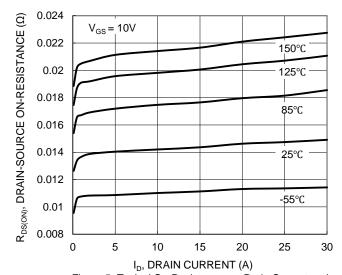
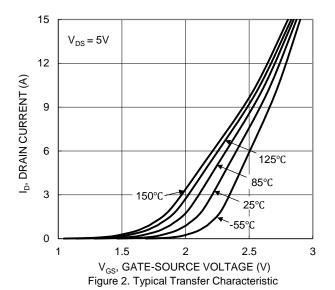
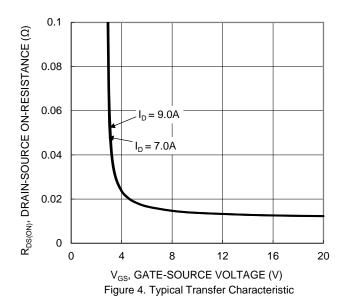


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





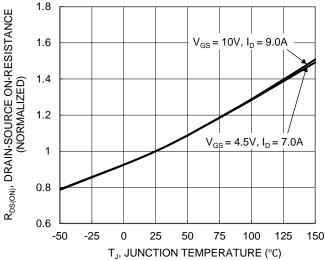


Figure 6. On-Resistance Variation with Junction Temperature



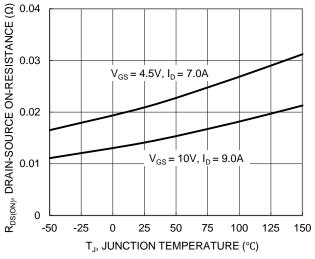
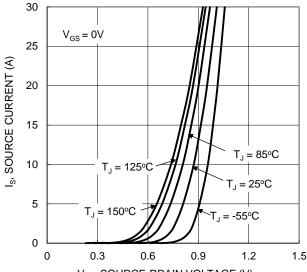


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

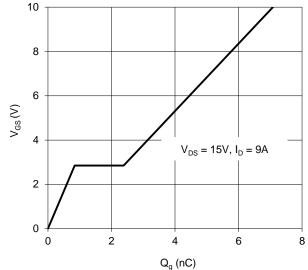


Figure 11. Gate Charge

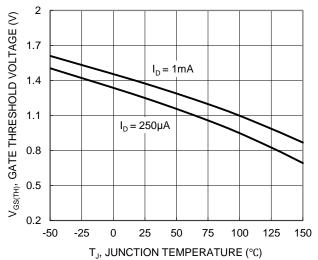
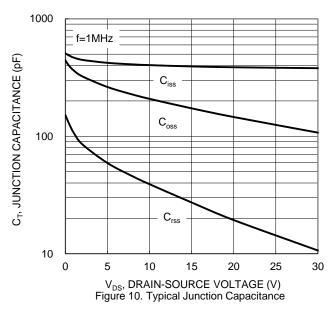


Figure 8. Gate Threshold Variation vs. Junction Temperature



100 $P_W = 100 \mu s$ $R_{DS(ON)}$ Limited $P_{,W} = 1 \text{ms}$ $P_W = 10ms$ 10 ID, DRAIN CURRENT (A) 1 0.1 $T_{J(Max)} = 150^{\circ}C T_C = 25^{\circ}C$ Single Pulse
DUT on 1*MRP Board DC V_{GS}= 10V 0.01 0.1 10 100

V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



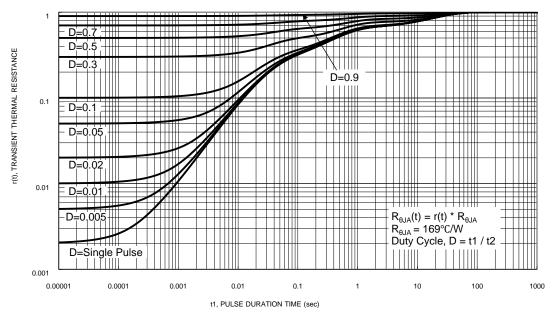


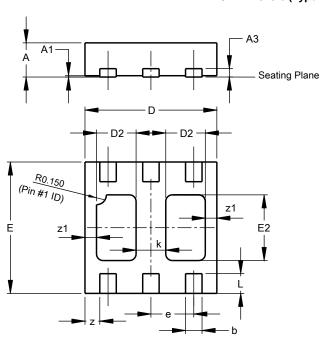
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

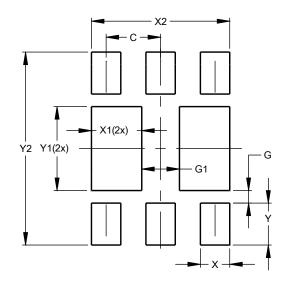


U-DFN2020-6								
Type B								
Dim	Min	Max	Тур					
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
A3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	0.50	0.70	0.60					
е	-	-	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	-	-	0.45					
L	0.25	0.35	0.30					
Z	-	-	0.225					
z1	-	-	0.175					
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value
Dillielisions	(in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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